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Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S15	1027	(430/331).CCLS.	US-PGPUB; USPAT	OR	OFF	2007/12/17 10:11
S24	1	("20060025809").PN.	US-PGPUB; USPAT	OR	OFF	2007/12/17 10:12
S23	0	("2006025809").PN.	US-PGPUB; USPAT	OR	OFF	2007/12/17 10:12
S26	1	("20020037946").PN.	US-PGPUB; USPAT	OR	OFF	2007/12/17 10:13
S25	1	("20060258809").PN.	US-PGPUB; USPAT	OR	OFF	2007/12/17 10:13
S27	0	("2006/0258809").URPN.	USPAT	OR	OFF	2007/12/17 10:22
S29	20156	trimethylammonium	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/12/17 10:23
S33	17	ethylmethylbenzylammonium	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/12/17 10:24
S32	0	dimethylbenzylethylammonium	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/12/17 10:24
S31	23	dimethylethylbenzylammonium	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/12/17 10:24
S30	6978	dimethylammonium	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/12/17 10:24
S36	9	benzylmethylmethylammonium	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/12/17 10:25

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S35	18	benzylethyldimethylammonium	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/12/17 10:25
S34	8	ethylbenzylidimethylammonium	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/12/17 10:25
S37	75	S31 S33 S34 S35 S36	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/12/17 10:26
S38	1	2005-152114.NRAN.	DERWENT	OR	OFF	2007/12/17 10:40
S39	45210	(S28 S29 S30) and (water aqueous aq)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/12/17 10:51
S28	26252	tetramethylammonium	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/12/17 10:51
S40	8085	(S28 S29 S30) and (water aqueous aq) and (\$crosslinking)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/12/17 10:52
S41	8731	(S28 S29 S30) and (water aqueous aq) and (\$crosslinking \$crosslinks \$crosslinkable \$crosslinker)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/12/17 10:53
S42	2544	(S28 S29 S30) and (water aqueous aq) and (\$crosslinking \$crosslinks \$crosslinkable \$crosslinker) and ("438"/\$.ccls. "430"/\$.ccls.)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/12/17 10:54
S44	0	("2004/0137378").URPN.	USPAT	OR	OFF	2007/12/17 14:22

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S47	6978	dimethylammonium	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/12/17 15:18
S46	20156	trimethylammonium	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/12/17 15:18
S45	26252	tetramethylammonium	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/12/17 15:18
S43	234	(S28 S29 S30) and 430/331.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/12/17 15:18
S49	1940	(S45 S46 S47) and 430/311-330.ccls. not 430/331.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/12/17 15:19
S48	2112	(S45 S46 S47) and 430/311-330.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/12/17 15:19
S50	263	sugeta.inv.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/12/19 14:49
S51	2	("20050123851").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/12/19 15:29
S52	1	2003-607971.NRAN.	DERWENT	OR	OFF	2007/12/19 15:30

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S53	23	(US-20070213447-\$ or US-20060263728-\$ or US-20060258809-\$ or US-20060099347-\$ or US-20060079628-\$ or US-20060003601-\$ or US-20050245663-\$ or US-20050175926-\$ or US-20050123851-\$ or US-20050058950-\$ or US-20040121615-\$ or US-20050009365-\$ or US-20040137378-\$ or US-20040137377-\$ or US-20040106737-\$ or US-20040104196-\$ or US-20040067452-\$ or US-20040067303-\$ or US-20030096903-\$ or US-20030087032-\$ or US-20030008968-\$).did. or (US-7189499-\$ or US-6811817-\$).did.	US-PGPUB; USPAT	OR	OFF	2007/12/19 15:53
S55	1	2004-351154.NRAN.	DERWENT	OR	OFF	2007/12/19 16:27
S54	2	jp-2004077951-\$..did.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/12/19 16:27
S56	0	("2003/0008968").URPN.	USPAT	OR	OFF	2007/12/20 10:36
S1	2	wo-9603407-\$..did.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/12/20 11:53

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L1	905	over adj coating adj agent or overcoating adj agent or "resist pattern thickening material" or "coated thermal flow process" or "thermal shrinkage" same "heat treatment"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/12/20 10:39
L2	1	2003WO-JP09867.ap,prai.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/12/20 11:10
L3	1	2005-181904.NRAN.	DERWENT	OR	OFF	2007/12/20 11:52
L4	21	"RELACS"	DERWENT	OR	OFF	2007/12/20 11:52
L5	2	JP-10073927-\$.did.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/12/20 11:53
L6	1	1998-064450.NRAN.	DERWENT	OR	OFF	2007/12/20 11:55
L7	1	("5858620").PN.	US-PGPUB; USPAT	OR	OFF	2007/12/20 11:55
L8	27	("5858620").URPN.	USPAT	OR	OFF	2007/12/20 13:37
L9	3333	"dimethylammonium chloride" "hydrochloric acid dimethylamine" "N-methylmethanamine hydrochloride" "dimethylamine hydrochloride"	USPAT	OR	OFF	2007/12/20 13:39

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L10	122	(US-20040137378-\$ or US-20040137377-\$ or US-20040121259-\$ or US-20040029047-\$ or US-20030170571-\$ or US-20060073419-\$ or US-20050123851-\$ or US-20050058950-\$ or US-20060258809-\$ or US-20010012596-\$ or US-20040018443-\$ or US-20060099347-\$ or US-20050245663-\$ or US-20050175926-\$ or US-20040229170-\$ or US-20020042022-\$ or US-20060079628-\$ or US-20060063077-\$ or US-20060003601-\$ or US-20020012866-\$ or US-20010031419-\$ or US-20010009746-\$ or US-20060263728-\$ or US-20040067452-\$ or US-20030017425-\$ or US-20040121615-\$).did. or (US-20040106737-\$ or US-20040104196-\$ or US-20040067303-\$ or US-20030096903-\$ or US-20030008968-\$ or US-20030087032-\$ or US-20070213447-\$ or US-20050009365-\$ or US-20070232077-\$ or US-20070123623-\$ or US-20070106021-\$ or US-20070048660-\$ or US-20060188807-\$ or US-20060188805-\$ or US-20060073420-\$ or US-20060046446-\$ or US-20050277054-\$ or US-20050031987-\$ or US-20040110099-\$ or US-20040096780-\$ or US-20040072098-\$ or US-20030157801-\$ or US-20030102285-\$).did. or (US-5585427-\$ or US-5155167-\$ or US-7067234-\$ or US-6998215-\$ or US-7045274-\$ or US-6709807-\$ or US-6403288-\$ or US-5561105-\$ or US-5516886-\$ or US-7150959-\$ or US-6746821-\$ or US-6692892-\$ or US-6582891-\$ or US-5611850-\$ or US-7189499-\$ or US-7198884-\$ or US-6969577-\$ or US-6365306-\$ or US-6764806-\$ or US-6534243-\$ or US-5795700-\$ or US-5541037-\$ or US-3996121-\$ or US-6811817-\$ or US-3615458-\$ or US-7235345-\$).did. or (US-7220628-\$ or US-7189783-\$ or US-5858620-\$ or US-6319853-\$ or US-6492075-\$ or US-6566040-\$ or US-6579657-\$ or US-6593063-\$ or US-6663761-\$ or US-7033735-\$ or US-7100275-\$ or US-7141177-\$ or US-7160665-\$).did. or (US-2856386-\$).did. or (EP-1837706-\$ or EP-1793274-\$ or EP-1757988-\$ or EP-1693709-\$ or EP-1542079-\$ or EP-1489463-\$ or EP-1469354-\$ or EP-1403717-\$ or EP-1398671-\$ or WO-2004017421-\$ or EP-1385059-\$ or EP-1376242-\$ or EP-1315043-\$).did. or (JP-06001810-\$ or JP-2007148272-\$ or JP-2007057967-\$ or JP-2007057709-\$ or JP-2006276865-\$ or JP-2006276864-\$ or JP-2006259692-\$ or JP-2006227633-\$ or JP-2006060006-\$ or JP-2005055873-\$ or JP-2004133192-\$ or JP-2004126080-\$ or JP-2004087967-\$ or JP-2004079707-\$ or JP-2004077951-\$ or JP-2004061668-\$ or JP-2004046060-\$ or JP-2003084448-\$).did. or (WO-2005008340-\$ or US-5858620-\$).did.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2007/12/20 13:38
L11	0	10 and 9	US-PGPUB; USPAT	OR	OFF	2007/12/20 13:39

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L12	0	9 same quencher	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/12/20 13:39
L13	453	9 and crosslink\$	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/12/20 13:40
L14	447	9 and crosslink\$ and (water aq aqueous)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/12/20 14:05
L18	801	(polyallylamine poly adj allylamine) same (water aq aqueous) and crosslink\$	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/12/20 14:12
L19	18	copoly with allylamine	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/12/20 14:13

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